

Reza Ghandi

List of Publications by Year in descending order

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citing authors

#	ARTICLE	IF	CITATIONS
1	Surface-Passivation Effects on the Performance of 4H-SiC BJTs. IEEE Transactions on Electron Devices, 2011, 58, 259-265.	3.0	57
2	Modeling and Characterization of Current Gain Versus Temperature in 4H-SiC Power BJTs. IEEE Transactions on Electron Devices, 2010, 57, 704-711.	3.0	56
3	Design and Characterization of High-Temperature ECL-Based Bipolar Integrated Circuits in 4H-SiC. IEEE Transactions on Electron Devices, 2012, 59, 1076-1083.	3.0	56
4	High-Voltage 4H-SiC PiN Diodes With Etched Junction Termination Extension. IEEE Electron Device Letters, 2009, 30, 1170-1172.	3.9	55
5	Fabrication of 2700-V 12- Ω Non Ion-Implanted 4H-SiC BJTs With Common-Emitter Current Gain of 50. IEEE Electron Device Letters, 2008, 29, 1135-1137.	3.9	35
6	Influence of Emitter Width and Emitter-Base Distance on the Current Gain in 4H-SiC Power BJTs. IEEE Transactions on Electron Devices, 2010, 57, 2664-2670.	3.0	26
7	High-Voltage (2.8 kV) Implantation-Free 4H-SiC BJTs With Long-Term Stability of the Current Gain. IEEE Transactions on Electron Devices, 2011, 58, 2665-2669.	3.0	26
8	Modeling and Characterization of the on-Resistance in 4H-SiC Power BJTs. IEEE Transactions on Electron Devices, 2011, 58, 2081-2087.	3.0	20
9	High-Current-Gain SiC BJTs With Regrown Extrinsic Base and Etched JTE. IEEE Transactions on Electron Devices, 2008, 55, 1894-1898.	3.0	18
10	4.5kV SiC Charge-Balanced MOSFETs with Ultra-Low On-Resistance. , 2020, , .		17
11	SiC Charge-Balanced Devices Offering Breakthrough Performance Surpassing the 1-D Ron versus BV Limit. Materials Science Forum, 0, 963, 655-659.	0.3	12
12	High Voltage, Low On-Resistance 4H-SiC BJTs with Improved Junction Termination Extension. Materials Science Forum, 2011, 679-680, 706-709.	0.3	8
13	3kV SiC Charge-Balanced Diodes Breaking Unipolar Limit. , 2019, , .		8
14	Experimental Evaluation of Different Passivation Layers on the Performance of 3kV 4H-SiC BJTs. Materials Science Forum, 2010, 645-648, 661-664.	0.3	7
15	SiC Bipolar Power Transistors - Design and Technology Issues for Ultimate Performance. Materials Research Society Symposia Proceedings, 2010, 1246, 1.	0.1	5
16	Effect of 3.0 MeV helium implantation on electrical characteristics of 4H-SiC BJTs. Physica Scripta, 2010, T141, 014012.	2.5	4
17	Fabrication of 2.5kV 4H-SiC PiN Diodes with High Energy Implantation (>12MeV) of Al ⁺ and B ⁺ . Materials Science Forum, 0, 924, 573-576.	0.3	4
18	Deep Level Transient Spectroscopy (DLTS) Study of 4H-SiC Schottky Diodes and PiN Diodes. Materials Science Forum, 0, 963, 516-519.	0.3	4

#	ARTICLE	IF	CITATIONS
19	Bipolar Integrated OR-NOR Gate in 4H-SiC. Materials Science Forum, 0, 717-720, 1257-1260.	0.3	2
20	Dynamic Switching of 3kV 4H-SiC Charge-Balanced Junction Barrier Schottky (JBS) Diodes. Materials Science Forum, 0, 1004, 939-944.	0.3	2
21	Measurements and Simulations of Lateral PNP Transistors in a SiC NPN BJT Technology for High Temperature Integrated Circuits. Materials Science Forum, 2011, 679-680, 758-761.	0.3	1
22	A Subcircuit SPICE Model for SiC Charge-Balance Schottky Diodes. Materials Science Forum, 0, 1004, 945-952.	0.3	1
23	(Invited) Silicon Carbide Bipolar Power Devices. ECS Transactions, 2011, 41, 189-200.	0.5	0